

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors







1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 (SC-73) surfacemountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capabiliy
- · Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ t _p = 20 ms; <u>Fig. 4; Fig. 5</u>	-	-	8	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	-	1	A
Static chara	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	-	3	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	-	-	3	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	3	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 9</u>	-	-	5	mA

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2
2	T2	main terminal 2		sym051
3	G	gate		
4	T2	main terminal 2	☐1 ☐2 ☐ 3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
Z0103MN	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

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7. Limiting values

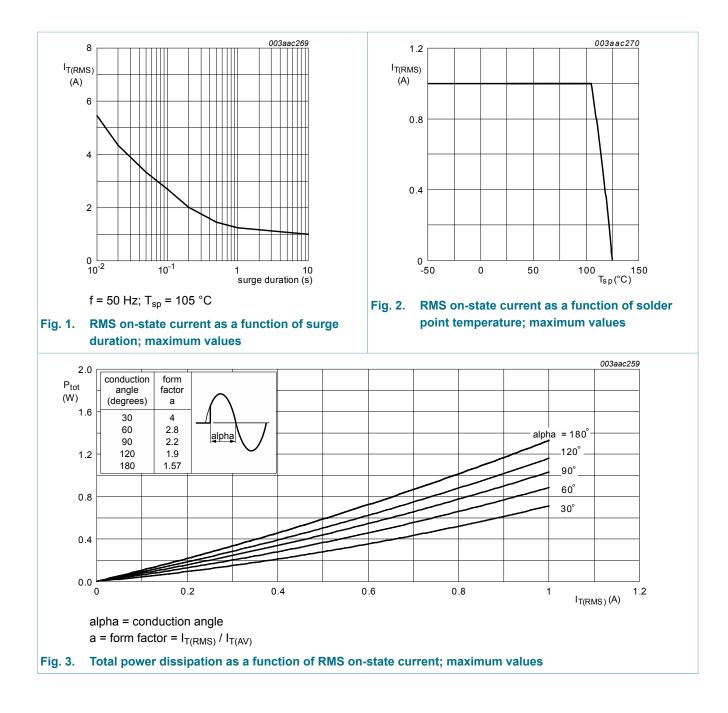
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 105 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	1	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; Fig. 4; Fig. 5$	-	8	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	8.5	A
l ² t	I2t for fusing	t _p = 10 ms; SIN	-	0.32	A ² s
dI _T /dt	rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 0.1 A/µs; T2+ G+	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 0.1 A/µs; T2+ G-	-	50	A/µs
		$I_T = 1 \text{ A}; I_G = 20 \text{ mA}; \text{ d}I_G/\text{d}t = 0.1 \text{ A}/\mu\text{s};$ T2- G-	-	50	A/µs
		$I_T = 1 \text{ A}; I_G = 20 \text{ mA}; \text{ d}I_G/\text{d}t = 0.1 \text{ A}/\mu\text{s};$ T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	А
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

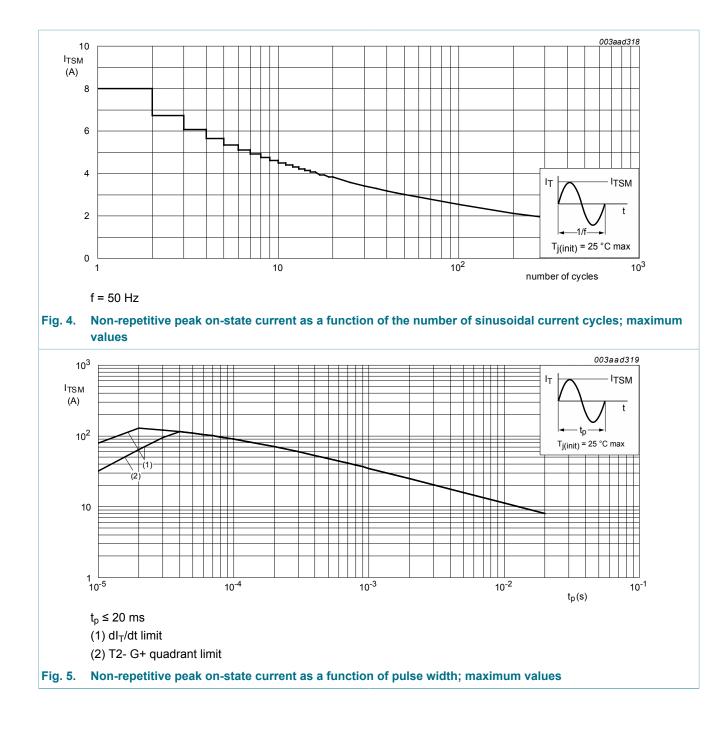
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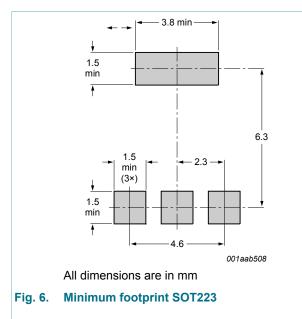
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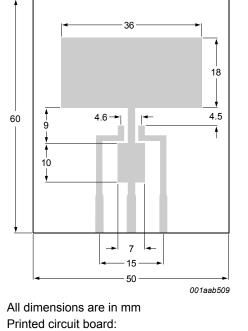


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8. Thermal characteristics

Table 5. Th	nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; <u>Fig. 8</u>	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to	full cycle; printed circuit board mounted; minimum footprint; Fig. 6	-	156	-	K/W
	ambient	full cycle; printed circuit board mounted; pad area; Fig. 7	-	70	-	K/W





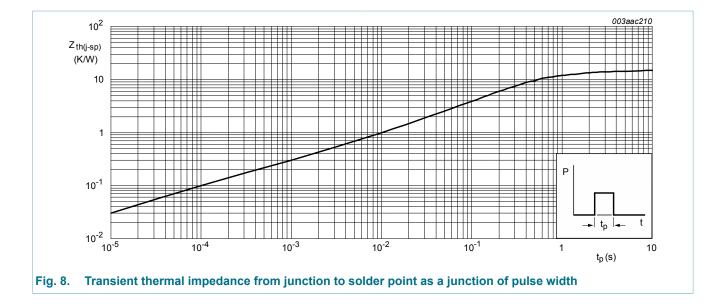
FR4 epoxy glass (1.6 mm thick), copper laminate (35 um thick)

Fig. 7. Printed circuit board pad area: SOT223

Product data sheet

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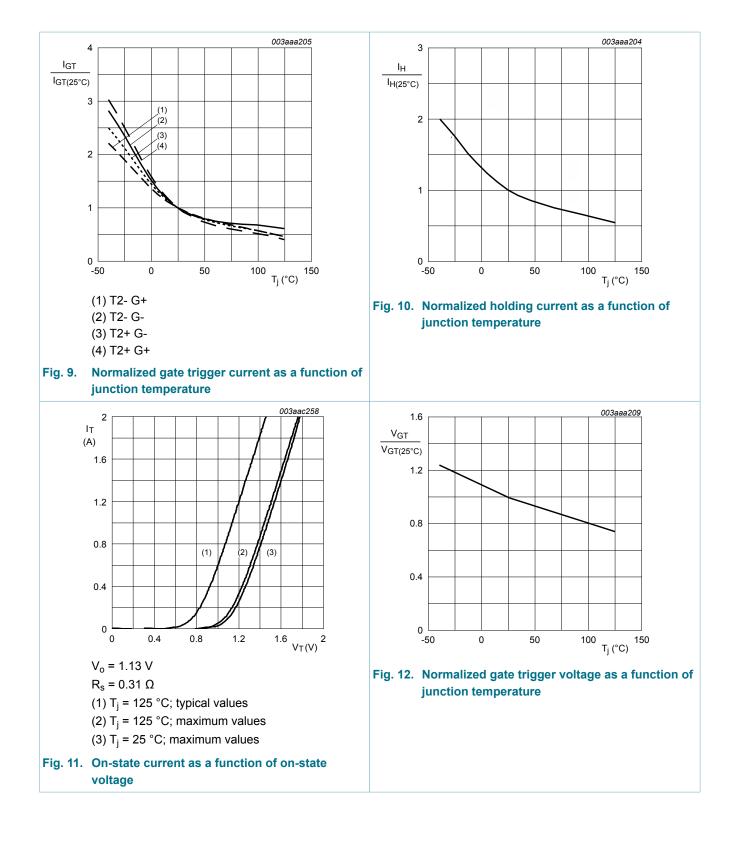
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9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·				
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 9}$	-	-	3	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	-	-	3	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 9</u>	-	-	3	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 9</u>	-	-	5	mA
lL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 10</u>	-	-	7	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 10</u>	-	-	15	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 10</u>	-	-	7	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$ T _j = 25 °C; Fig. 10	-	-	7	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	7	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 11</u>	-	1.3	1.6	V
V _{GT}	gate trigger voltage	$V_D = 600 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T}_j = 125 ^\circ\text{C}$	0.2	-	-	V
		V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 12	-	-	1	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	-	0.5	mA
Dynamic ch	naracteristics		I			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 110 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit; Fig. 13	10	-	-	V/µ
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T _j = 110 °C; dI _{com} / dt = 0.44 A/ms; gate open circuit	0.5	-	-	V/µs

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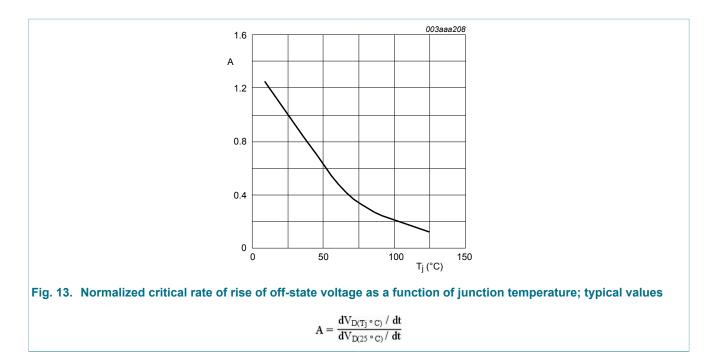
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Product data sheet

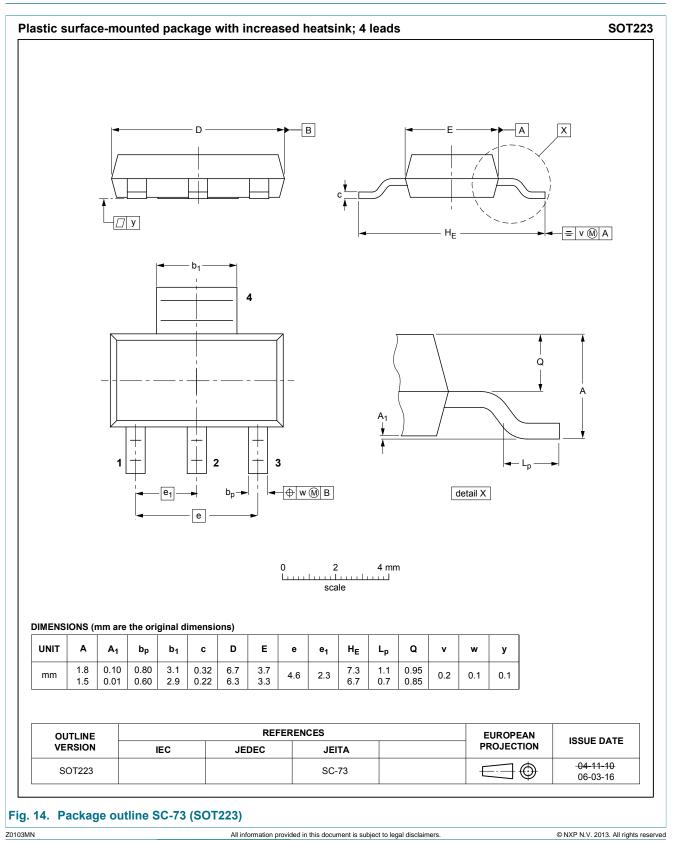
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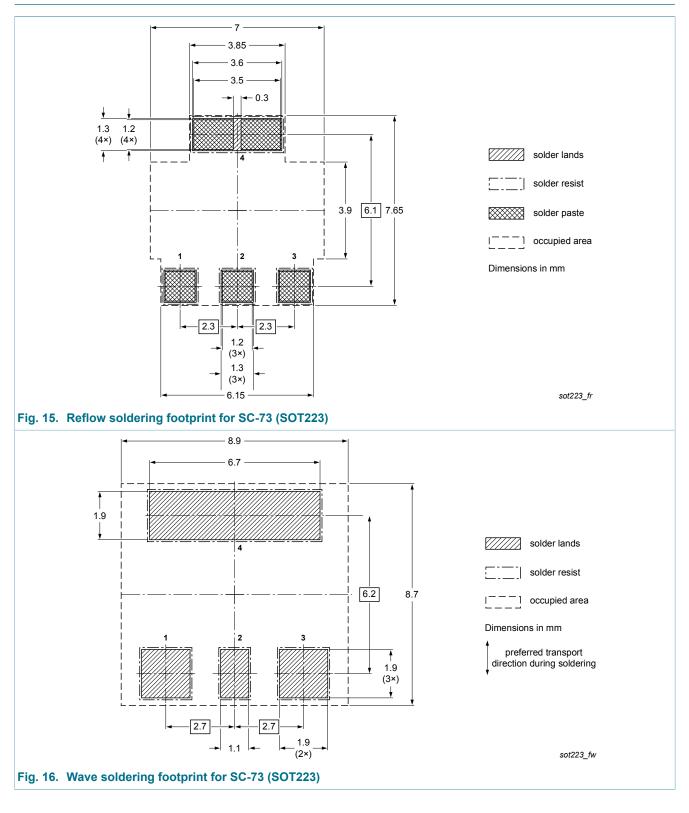
10. Package outline



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11. Soldering



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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